

N-Channel Power MOSFET

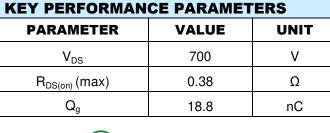
700V, 11A, 0.38Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

APPLICATION

- Power Supply
- Lighting

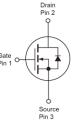












Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	ITO-220	IPAK/DPAK	UNIT
Drain-Source Voltage		V _{DS}	700		V
Gate-Source Voltage		V _{GS}	±30		V
Quit Dui Quit (Note 1)	T _C = 25°C		11		A
Continuous Drain Current (Note 1)	T _C = 100°C		6.6		
Pulsed Drain Current (Note 2)		I _{DM}	33		А
Total Power Dissipation @ $T_c = 25^{\circ}C$		P _{DTOT}	33	125	W
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	156		mJ
Single Pulsed Avalanche Current (Note 3)		I _{AS}	2.5		А
Operating Junction and Storage Temperature Range		T_J,T_STG	- 55 to +150		°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ITO-220	IPAK/DPAK	UNIT
Junction to Case Thermal Resistance	R _{eJC}	3.8	1	°C/W
Junction to Ambient Thermal Resistance	R _{eja}	62 °C		°C/W

Notes: R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{BJA} is guaranteed by design while R_{BCA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 PCB in still air.





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ELECTRICAL SPECIFICA	TIONS (T _A = 25°C unles	s otherwise no	oted)			
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)				•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 3.3A$	R _{DS(on)}		0.33	0.38	Ω
Dynamic (Note 5)				•		
Total Gate Charge		Qg		18.8		nC
Gate-Source Charge	$V_{DS} = 380V, I_D = 11A,$	Q _{gs}		3.7		
Gate-Drain Charge	$V_{GS} = 10V$	Q _{gd}		5.6		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		981		
Output Capacitance	f = 1.0MHz	C _{oss}		58		pF
Gate Resistance	F = 1MHz, open drain	R _g		3.3		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 35\Omega,$ $I_{D} = 11A, V_{GS} = 10V,$	t _{d(on)}		32		
Turn-On Rise Time		tr		21		
Turn-Off Delay Time		t _{d(off)}		62		ns
Turn-Off Fall Time		t _f		28		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_{\rm S} = 11 {\rm A}, V_{\rm GS} = 0 {\rm V}$	V _{SD}			1.4	V
Reverse Recovery Time	V _B =200V, I _S = 5.5A	t _{rr}		226		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		2.1		μC

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 50mH, I_{AS} = 2.5A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM70N380CI C0G	ITO-220	50pcs / Tube
TSM70N380CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N380CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

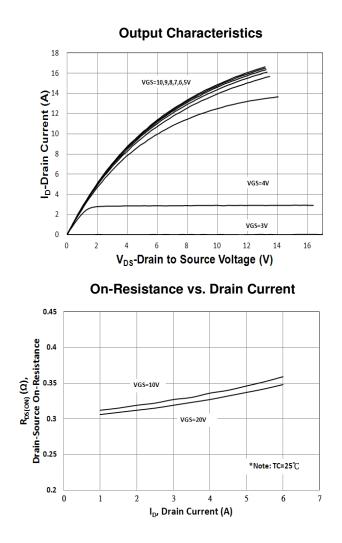
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

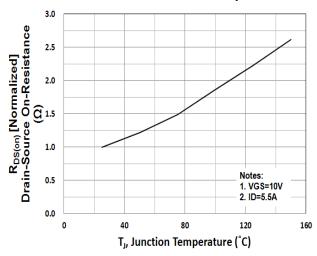


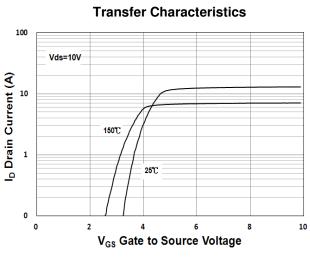
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

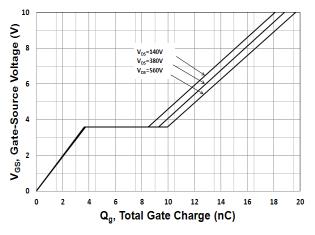


On-Resistance vs. Junction Temperature

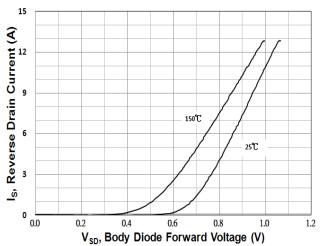




Gate-Source Voltage vs. Gate Charge



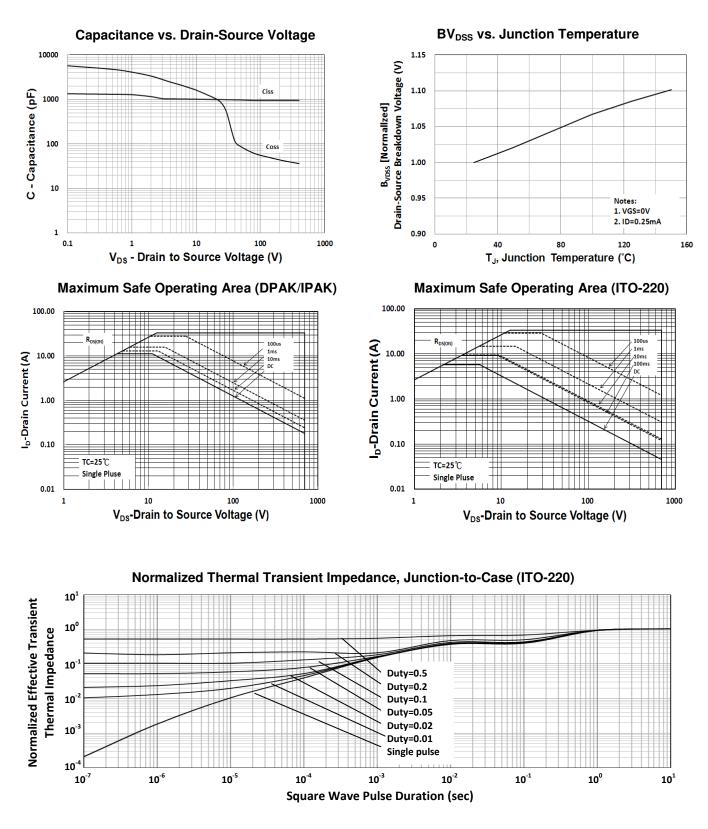
Source-Drain Diode Forward Current vs. Voltage





CHARACTERISTICS CURVES

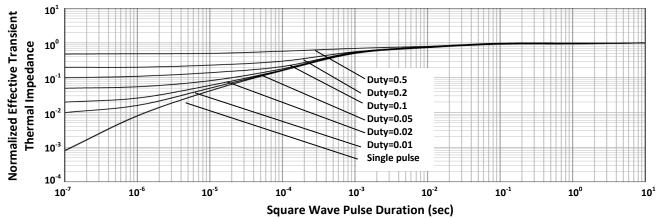
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$





ELECTRICAL CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)

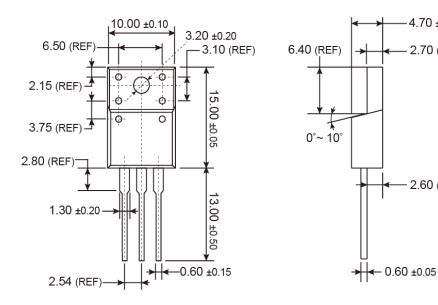


4.70 ±0.10

2.70 (REF)

2.60 (REF)

PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM

TAIWAN

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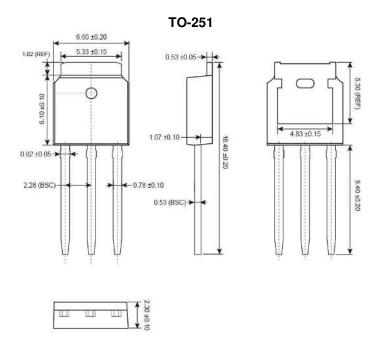


- **G** = Halogen Free
- Y = Year Code
- **WW** = Week Code $(01 \sim 52)$
 - = Factory Code F

ITO-220



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



R =Apr

V =Aug Z =Dec

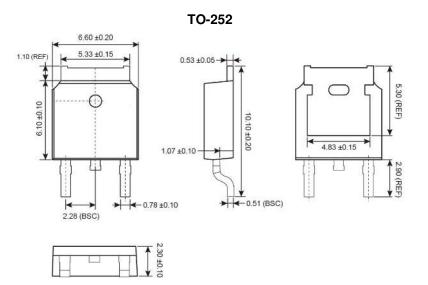
MARKING DIAGRAM

	Y = Year Code	
5	M = Month Code for Halogen Free Produ	ıct
70N380	O =Jan P =Feb Q =Mar	R
	S =May T =Jun U =Jul	V
	W =Sep X =Oct Y =Nov	Ζ
	L = Lot Code (1~9, A~Z)	
#1∐ ∐ ∐		

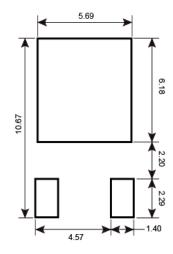




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM

	Y = Year Code
5	M = Month Code for Halogen Free Product
70N380	O =Jan P =Feb Q =Mar R =Apr
YML	S =May T =Jun U =Jul V =Aug
() [] ()	W =Sep X =Oct Y =Nov Z =Dec
#1∐ ∐	$L = Lot Code (1 \sim 9, A \sim Z)$



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